

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Thomas A. Figura et al.

Title: USE OF A PLASMA SOURCE TO FORM A LAYER DURING THE FORMATION OF A SEMICONDUCTOR DEVICE

Docket No.: 303.932US4

Serial No.: 09/471,460

Filed: December 22, 1999

Due Date: September 27, 2006

Examiner: Calvin Lee

Group Art Unit: 2818

MS AF

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

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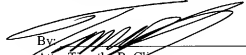
X Amendment and Response Under 37 CFR 1.116 (10 pgs.).

X Communication Concerning Related Applications (1 pg.).


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SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

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Name


Signature

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

(GENERAL)

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FORMATION OF A SEMICONDUCTOR DEVICE

COMMUNICATION CONCERNING RELATED APPLICATION(S)**MS Amendment**

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Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date/Issue Date</u>	<u>Attorney Docket</u>	<u>Title</u>
09470650 6716769	December 22, 1999	303.932US5	USE OF A PLASMA SOURCE TO FORM A LAYER DURING THE FORMATION OF A SEMICONDUCTOR DEVICE
09470651	December 22, 1999	303.932US6	USE OF A PLASMA SOURCE TO FORM A LAYER DURING THE FORMATION OF A SEMICONDUCTOR DEVICE


Continuations and divisionals may be later filed on the cases listed above, or cited to the Examiner in any previous Communication Concerning Related Applications. Applicants request that the Examiner review all continuations and divisionals of the above-listed or previously-cited patent applications before allowing the claims of the present patent application.

Respectfully submitted,
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By Applicants' Representatives,
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Name

KATE GANNON

Signature

